# 2N1483, 2N1484, 2N1485,



### **NPN Medium Power Silicon Transistor**

Rev. V2

#### **Features**

- Available in JAN, JANTX and JANTXV per MIL-PRF-19500/180
- TO-8 Package
- Ideal For Medium Power Applications That Require High Frequency Switching in a Low Profile Package



### Electrical Characteristics $T_c = +25^{\circ}C$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.
Collector - Emitter Breakdown Voltage	I <sub>C</sub> = 100 mA dc 2N1483, 2N1485 2N1484, 2N1486	2N1483, 2N1485 2N1484, 2N1486			
Collector - Emitter Breakdown Voltage	$V_{EB}$ = 1.5 V dc, $I_{C}$ = 0.25 mA dc 2N1483, 2N1485 2N1484, 2N1486	V <sub>(BR)CEX</sub>	V dc		60 100
Collector - Base Breakdown Voltage	I <sub>C</sub> = 100 μA dc 2N1483, 2N1485 2N1484, 2N1486	V <sub>(BR)CBO</sub>	V dc	_	60 100
Emitter - Base Cutoff Current	V <sub>EB</sub> = 12 V dc	I <sub>EBO</sub>	μA dc	_	15
Collector - Emitter Cutoff Current	V <sub>EB</sub> = 1.5 V dc V <sub>CB</sub> = 60 V dc, 2N1483, 2N1485 V <sub>CB</sub> = 100 V dc, 2N1484, 2N1486	I <sub>CEX</sub>	mA dc		.25 .25
Collector - Base Cutoff Current	V <sub>CB</sub> = 30 V dc, 2N1483, 2N1485 V <sub>CB</sub> = 50 V dc, 2N1484, 2N1486	I <sub>CBO1</sub>	μA dc		15 15
		<u> </u>			
Forward Current Transfer Ratio	V <sub>CE</sub> = 4.0 Vdc, I <sub>C</sub> = 750 mA dc 2N1483, 2N1484 2N1485, 2N1486	h <sub>FE2</sub>	-	20 35	60 100
Base - Emitter Voltage (non-saturated)	$V_{CE}$ = 4.0V dc, $I_{C}$ = 750 mA dc	$V_{BE}$	V dc		2.0
Collector - Emitter Saturation Voltage	Ic = 750 mA dc I <sub>B</sub> = 75 mA dc 2N1483, 2N1484 I <sub>B</sub> = 40 mA dc 2N1485, 2N1486	V <sub>CE(SAT)</sub>	V dc	_	1.20 0.75

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## Electrical Characteristics (T<sub>C</sub> = +25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Units	Min.	Max.			
Collector - Base Cutoff Current	V <sub>CB</sub> = 60 V dc, 2N1483, 2N1485 V <sub>CB</sub> = 100 V dc, 2N1484, 2N1486	I <sub>CBO3</sub>	μA dc	_	100 100			
Collector - Base Cutoff Current	T <sub>A</sub> = +175°C V <sub>CB</sub> = 30 V dc, 2N1483, 2N1485 V <sub>CB</sub> = 50 V dc, 2N1484, 2N1486	I <sub>CBO2</sub>	mA		1.0 1.0			
Forward - Current Transfer Ratio	$T_A = -55^{\circ}\text{C}$ $V_{CE} = 4.0 \text{ V dc}, I_C = 750 \text{ mA dc}$ $2\text{N}1483, 2\text{N}1484$ $2\text{N}1485, 2\text{N}1486$	h <sub>FE2</sub>	-	10 17				
Dynamic Characteristics								
Small Signal, Short Circuit, Forward-Current Transfer Ratio Cutoff Frequency	$V_{CB}$ = 28 V dc, $I_{C}$ = 5.0 mA dc	f <sub>hfb</sub>	kHz	600				
Open Circuit Output Capacitance	C <sub>obo</sub>	pF	_	400				
Switching Characteristics								
Pulse Response	$V_{CC}$ = +12V dc, R <sub>C</sub> = 15.9 $\Omega$ , $I_{B0}$ = $I_{B2}$ = 35 mA dc; $I_{B1}$ = 65 mA dc	t <sub>on</sub> + t <sub>off</sub>	μs	_	25			

## Absolute Maximum Ratings (T<sub>A</sub> = +25°C unless otherwise specified)

Ratings	Symbol	2N1483 2N1485	2N1484 2N1486		
Collector - Emitter Voltage	$V_{\text{CEO}}$	40 V dc	55 V dc		
Collector - Base Voltage	$V_{CBO}$	60 V dc	100 V dc		
Emitter - Base Voltage	V <sub>EBO</sub>	12	V dc		
Collector Current	I <sub>C</sub>	3.0	3.0 A dc		
Total Power Dissipation  @ $T_A = 25^{\circ}C^{(1)}$ @ $T_C = 25^{\circ}C^{(2)}$	P <sub>T</sub>		5 W W		
Operating & Storage Temperature Range	$T_J$ , $T_{STG}$	-65°C to +200°C			

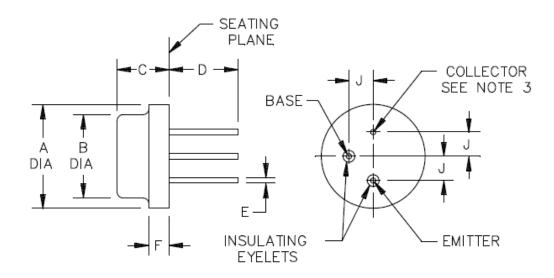
<sup>(1)</sup> Derate linearly 0.010 W/°C for  $T_A > +25$ °C (2) Derate linearly 0.143 W/°C for  $T_C > +25$ °C



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#### **Outline Drawing (TO-8)**



		Dimen	sions				Dimensions				
LTR Inches		Millimeters		Notes	LTR	Inches		Millimeters		Notes	
	Min	Max	Min	Max			Min	Max	Min	Max	
Α	.550	.650	13.97	16.51		E	.027	.033	0.69	0.84	3, 4
В	.444	.524	11.28	13.31		F		.115		2.92	
С	.270	.330	6.86	8.38		J	.136	.146	3.45	3.71	
D	.360	.440	9.14	11.18	3						

#### NOTES:

- 1. Dimensions are in inches. Millimeters are given for general information only.
- The collector shall be internally connected to the case.
- 3. All three leads.
- 4. Measured in the zone beyond .050 (1.27 mm) front the seating plane.

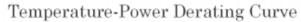
FIGURE 1. Dimensions and configuration of TO-8 package.



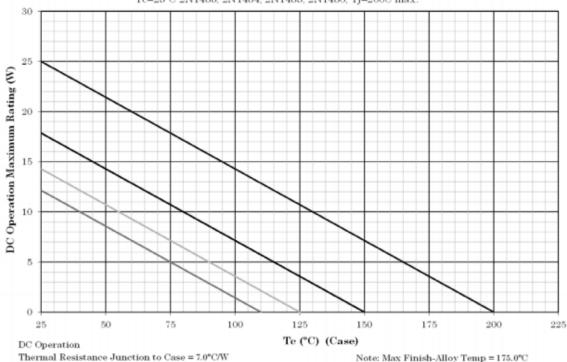
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#### **Temperature Derating Curve**







#### NOTES:

- This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at less than or equal to T<sub>J</sub> specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T<sub>J</sub> allowed.
- Derate design curve constrained by the maximum junction temperature (T<sub>J</sub> ≤ +200°C) and power rating specified. (See 1.3 herein.)
- Derate design curve chosen at T<sub>J</sub> ≤ +150°C, where the maximum temperature of electrical test is performed.
- Derate design curves chosen at T<sub>J</sub> ≤ +125°C, and +110°C to show power rating where most users want to limit T<sub>J</sub> in their application.

FIGURE 2. Temperature-power derating graph.

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